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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of) Examiner: S. H. Versteeg
GOPALRAJA, et al.)
Serial No.: 10/632,882) Art Unit: 1753
Filed: 31 July 2003)

For: SELF-IONIZED AND CAPACITIVELY-COUPLED PLASMA FOR SPUTTERING AND
RESPUTTERING

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with 37 CFR 1.56, 1.97, and 1.98, enclosed please find Form PTO-1449 listing the attached references which might be deemed material to the examination of the above-identified application.

A. Non-English Language References

- Enclosed is a search report for a counterpart application.
- The search report Examiner has provided comments on the relevance of any non-English language references cited in the search report.
- The specification incorporates comments on the relevance of non-English language references.
- Set forth below are comments provided by the applicant's home country counsel on the relevance of non-English language references:

B. The information disclosure statement submitted herewith is being filed

- Within three months of the filing date of a national application or request for continued examination under 37 CFR 1.114.
- Within three months of the date of entry into the national stage as set forth in 37 CFR 1.491 in an international application.
- Before the mailing date of a first Office Action on the merits.
- Before the mailing date of a first Office Action after filing of a request for continued examination.

C. The information disclosure statement submitted herewith is being filed after the period specified in paragraph B, but before the mailing date of a final action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or any other action otherwise closing prosecution, and is accompanied by:

- A statement under 37 CFR 1.97(e); *or*
- A fee of \$180 as set forth in 37 CFR 1.17(p).

D. The information disclosure statement submitted herewith is being filed after the period specified in paragraph C, but before payment of the issue fee, and is accompanied by:

- A statement under 37 CFR 1.97(e); *and*
- A fee of \$180 as set forth in 37 CFR 1.17(p).

STATEMENT UNDER 37 CFR 1.97(e)

I, the person signing below, certify:

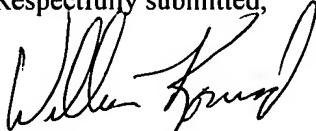
- That each item of information contained in the information disclosure statement submitted herewith was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the statement (37 CFR 1.97(e)(1)).
- That no item of information contained in the information disclosure statement submitted herewith was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the statement (37 CFR 1.97(e)(2)).

- continued -

If a fee is required under paragraph B or C *supra*, enclosed is Applicant's check in the amount of \$180 as set forth in 37 CFR 1.17(p). The Commissioner is authorized to charge any insufficiency or credit any overpayment related to this paper to Deposit Account 50-0585.

The Examiner is invited to contact the undersigned with any questions in this regard.

Respectfully submitted,



19 March 2007

(Date)

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I hereby certify that this correspondence is being deposited with the United States Postal Service on the date indicated above and is addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.



March 19, 2007

(Date)

O I P E
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P A T E N T D I S C L O S U R E C I T A T I O N
I N A N A P P L I C A T I O N

FORM PTO-1449		MAR 22 2007		Docket Number (Optional) 006775USA	Application Number 10/632,882
INFORMATION DISCLOSURE CITATION IN AN APPLICATION				Applicant GOPALRAJA et al.	
7082	(Use several sheets if necessary)		Filing Date July 31, 2003	Group Art Unit 1753	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE
	6	6	1	0	1	8	4	8/26/03	Ding, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	Translation	
												YES	NO
	03	0	4	2	4	2	4	5/22/03	PCT				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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